

FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		DOCKET NO: 007352 USA/ETCH/DRIE/JB		APPLICATION NO.: 10/615,159										
INFORMATION DISCLOSURE STATEMENT IN AN APPLICATION		APPLICANT: Frum et al.			GROUP ART UNIT: 1763									
		FILING DATE: 7/7/2003												
U.S. PATENT DOCUMENTS														
EXAMINER INITIAL	DOCUMENT NUMBER								DATE	NAME	CLASS	SUB- CLASS	FILING DATE IF APPROPRIATE	
GAG	5	4	5	0	2	0	5	09/12/1995	Sawin, et al.					
	5	5	0	3	7	0	7	04/02/1996	Maung, et al.					
	5	5	6	4	8	3	0	10/15/1996	Bobel, et al.					
	5	6	5	8	4	1	8	08/19/1997	Coronel, et al.					
	5	7	5	6	4	0	0	05/26/1998	Ye, et al.					
	6	0	8	1	3	3	4	06/27/2000	Grimbergen, et al.					
	6	1	6	5	3	1	1	12/26/2000	Collins, et al.					
	4	1	4	7	4	3	5	04/30/1979	Habegger					
	4	8	4	6	9	2	8	07/11/1989	Dolins, et al.					
GAG	4	8	4	7	7	9	2	07/11/1989	Bama, et al.					
FOREIGN PATENT DOCUMENTS														
	DOCUMENT NUMBER								DATE	COUNTRY	CLASS	SUB- CLASS	TRANSLATION	
												YES	NO	
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)														
GAG	Maynard, et al., "Multiwavelength Ellipsometry for Real-time Process Control of the Plasma Etching of Patterned Samples." J. Vac Sci Technol. B. 15 (1), Jan/Feb 1997, pages 109-115 ✓													
GAG	Klemens, F.P., et al., "High Density Plasma Gate Etching of 0.12 µm Devices with Sub 1.5 nm Gate-Oxides." Electrochemical Society Proceedings. Volume 97-30, pages 85-95													
EXAMINER	George Goudreau										DATE CONSIDERED		5-041	
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.														